PBSS5240X

40 V, 2 A PNP low VCEsat (BISS) transistor

19 October 2012

Product data sheet

1. Product profile

1.1 General description

PNP low V_{CEsat} Breakthrough In Small Signal (BISS) transistor in a medium power and flat lead SOT89 Surface-Mounted Device (SMD) plastic package. NPN complement: PBSS4240X.

1.2 Features and benefits

- Low collector-emitter saturation voltage V_{CEsat}
- High collector current capability I_C and I_{CM}
- · High efficiency due to less heat generation

1.3 Applications

- DC-to-DC conversion
- Supply line switching
- Battery charger
- LCD backlighting
- Driver in low supply voltage applications (e.g. lamps and LEDs)
- Inductive load driver (e.g. relays, buzzers and motors)

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{CEO}	collector-emitter voltage	open base	-	-	-40	V
I _C	collector current		-	-	-2	Α
I _{CM}	peak collector current		-	-	-3	Α
R _{CEsat}	collector-emitter saturation resistance	I_C = -1 A; I_B = -100 mA; pulsed; $t_p \le 300$ μs; $\delta \le 0.02$; T_{amb} = 25 °C	-	-	310	mΩ
I _{CRM}	repetitive peak collector current	$t_p \le 20 \text{ ms}; \delta \le 0.33 \; ; \text{pulsed}$	-	-	-2.5	Α



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2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	E	emitter		C
2	С	collector		В—
3	В	base	3 2 1	
			SOT89	sym132

3. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
PBSS5240X	SOT89	plastic surface-mounted package; die pad for good heat transfer; 3 leads	SOT89			

4. Marking

Table 4. Marking codes

3	
Type number	Marking code
PBSS5240X	S48

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{CBO}	collector-base voltage	open emitter		-	-40	V
V _{CEO}	collector-emitter voltage	open base		-	-40	V
V _{EBO}	emitter-base voltage	open collector		-	-5	V
I _C	collector current			-	-2	Α
I _{CRM}	repetitive peak collector current	$\delta \le 0.33$; $t_p \le 20$ ms; pulsed		-	-2.5	Α
I _{CM}	peak collector current			-	-3	Α
I _B	base current			-	-300	mA
I _{BM}	peak base current			-	-1	Α
P _{tot}	total power dissipation		[1]	-	0.5	W
			<u>[2]</u>	-	0.95	W

PBSS5240X

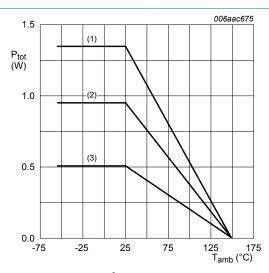
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Symbol	Parameter	Conditions		Min	Max	Unit
			[3]	-	1.35	W
T _j	junction temperature			-	150	°C
T _{amb}	ambient temperature			-65	150	°C
T _{stg}	storage temperature			-65	150	°C

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².



- (1) FR4 PCB, mounting pad for collector 6 cm²
- (2) FR4 PCB, mounting pad for collector 1 cm²
- (3) FR4 PCB, standard footprint

Fig. 1. Power derating curves

6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance		[1]	-	-	250	K/W
from jun ambient	from junction to		[2]	-	-	132	K/W
	ambient		[3]	-	-	93	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	-	16	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².

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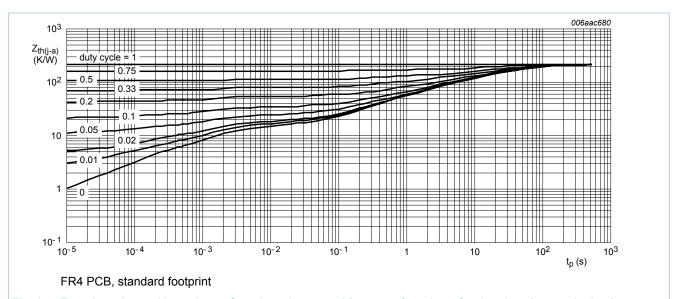


Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

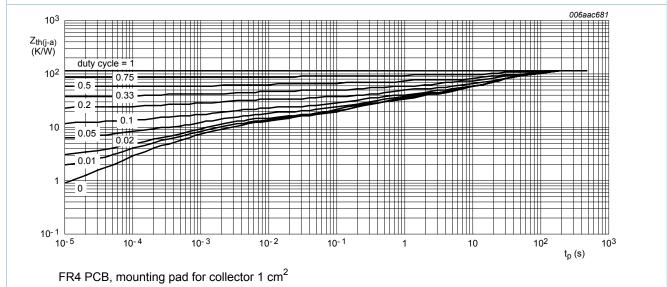
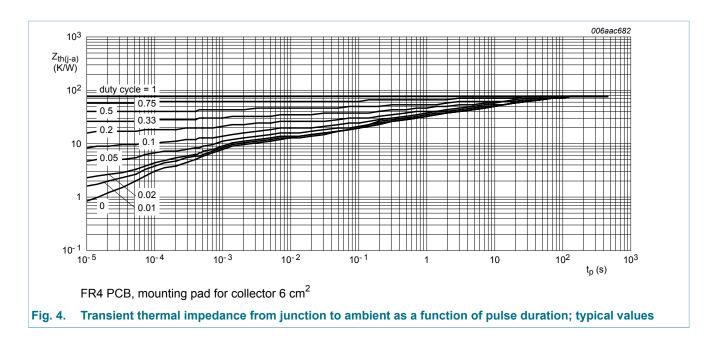


Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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7. Characteristics

Table 7. Characteristics

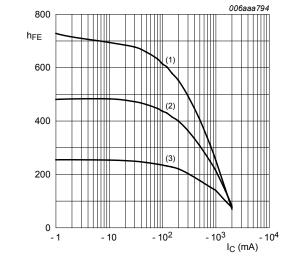
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I_{CBO}	collector-base cut-off	V _{CB} = -40 V; I _E = 0 A; T _{amb} = 25 °C	-	-	-100	nA
	current	V _{CB} = -40 V; I _E = 0 A; T _j = 150 °C	-	-	-50	μA
I _{CEO}	collector-emitter cut-off current	V _{CE} = -30 V; I _B = 0 A; T _{amb} = 25 °C	-	-	-100	nA
I _{EBO}	emitter-base cut-off current	V _{EB} = -5 V; I _C = 0 A; T _{amb} = 25 °C	-	-	-100	nA
h _{FE}	DC current gain	V_{CE} = -5 V; I_{C} = -1 mA; T_{amb} = 25 °C	300	-	-	
		V _{CE} = -5 V; I _C = -500 mA; T _{amb} = 25 °C	215	-	-	
		V _{CE} = -5 V; I _C = -1 A; T _{amb} = 25 °C	145	-	-	
		V_{CE} = -5 V; I_{C} = -2 A; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02 ; T_{amb}$ = 25 °C	55	-	-	
V _{CEsat}	collector-emitter	I _C = -100 mA; I _B = -5 mA; T _{amb} = 25 °C	-	-	-140	mV
	saturation voltage	I_{C} = -500 mA; I_{B} = -50 mA; T_{amb} = 25 °C	-	-	-170	mV
		I_{C} = -1 A; I_{B} = -100 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02 \ ; T_{amb}$ = 25 °C	-	-	-310	mV
		I_{C} = -2 A; I_{B} = -200 mA; pulsed; $t_{p} \le 300 \ \mu s$; $\delta \le 0.02$; T_{amb} = 25 °C	-	-	-630	mV
R _{CEsat}	collector-emitter saturation resistance	I_{C} = -1 A; I_{B} = -100 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02 ; T_{amb}$ = 25 °C	-	-	310	mΩ

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{BEsat}	base-emitter saturation voltage	I_{C} = -1 A; I_{B} = -100 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02 \ ; \ T_{amb}$ = 25 °C	-	-	-1.2	V
V _{BEon}	base-emitter turn-on voltage	$V_{CE} = -5 \text{ V; } I_{C} = -1 \text{ A; pulsed;}$ $t_{p} \le 300 \text{ µs; } \delta \le 0.02 \text{ ; } T_{amb} = 25 \text{ °C}$	-	-	-1.1	V
f _T	transition frequency	V_{CE} = -10 V; I_{C} = -50 mA; f = 100 MHz; T_{amb} = 25 °C	150	-	-	MHz
C _c	collector capacitance	V_{CB} = -10 V; I_{E} = 0 A; i_{e} = 0 A; f = 1 MHz; T_{amb} = 25 °C	-	-	12	pF



 $V_{CE} = -5 V$

(1) T_{amb} = 100 °C

(2) T_{amb} = 25 °C

(3) $T_{amb} = -55 \,^{\circ}C$

Fig. 5. DC current gain as a function of collector current; typical values

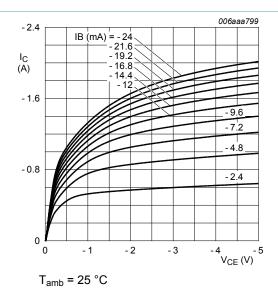
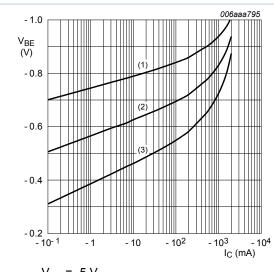


Fig. 6. Collector current as a function of collectoremitter voltage; typical values

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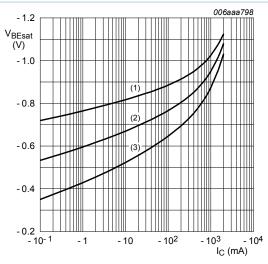
$$V_{CE} = -5 V$$

(1)
$$T_{amb} = -55$$
 °C

(2)
$$T_{amb}$$
 = 25 °C

(3)
$$T_{amb}$$
 = 100 °C

Fig. 7. Base-emitter voltage as a function of collector current; typical values



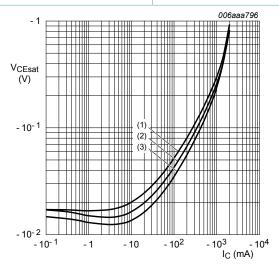
$$I_{\rm C}/I_{\rm B} = 20$$

(1)
$$T_{amb} = -55$$
 °C

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = 150 \, ^{\circ}C$$

Fig. 8. Base-emitter saturation voltage as a function of collector current; typical values



$$I_{\rm C}/I_{\rm B} = 20$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

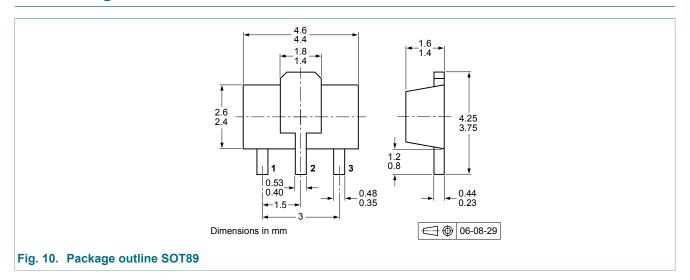
(2)
$$T_{amb}$$
 = 25 °C

$$(3) T_{amb} = -55 °C$$

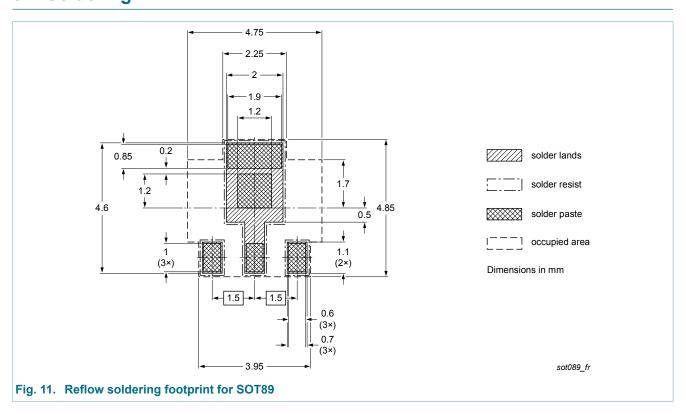
Collector-emitter saturation voltage as a function of collector current; typical values Fig. 9.

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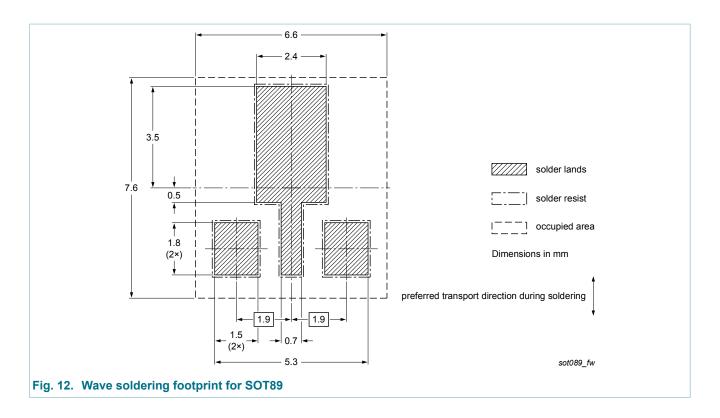
8. Package outline



9. Soldering



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10. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PBSS5240X v.1	20121019	Product data sheet	-	-

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